Roger Loo

List of Publications by Year
in descending order

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445	6,107	126907 33	155660 55
papers	citations	h-index	g-index

448	448	448	3664
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Simultaneous Dimensional and Analytical Characterization of Ordered Nanostructures. Small, 2022, 18, e2105776.	10.0	7
2	B and Ga Co-Doped Si_{1â^’x}Ge_x for p-Type Source/Drain Contacts. ECS Journal of Solid State Science and Technology, 2022, 11, 024008.	1.8	0
3	Stress in Siliconâ€“Germanium Nanowires: Layout Dependence and Imperfect Source/Drain Epitaxial Stressors. IEEE Transactions on Electron Devices, 2021, 68, 5380-5385.	3.0	5
4	Epitaxial Growth of Active Si on Top of SiGe Etch Stop Layer in View of 3D Device Integration. ECS Journal of Solid State Science and Technology, 2021, 10, 014001.	1.8	2
5	Extended Carrier Lifetime in Epitaxial Ge-on-Nothing Virtual Substrates. ECS Meeting Abstracts, 2021, MA2021-01, 1103-1103.	0.0	0
6	(Invited) Strain-Related Peculiarities of B Incorporation in Epitaxial Si1-XGex Source/Drain Materials and Their Impact on Electrical Properties. ECS Meeting Abstracts, 2021, MA2021-01, 1096-1096.	0.0	0
7	GaInP solar cells grown on Ge-on-Ge engineered substrates. , 2021, , .		3
8	Epitaxial Ge-on-Nothing and Epitaxial Ge on Si-on-Nothing as Virtual Substrates for 3D Device Stacking Technologies. ECS Journal of Solid State Science and Technology, 2021, 10, 084003.	1.8	1
9	Point defect formation near the epitaxial Ge(001) growth surface and the impact on phosphorus doping activation. Journal of Applied Physics, 2021, 130, 125702.	2.5	0
10	Effect of Strain on the Epitaxy of B-Doped Si0.5Ge0.5 Source/Drain Layers. ECS Transactions, 2021, 104, 167-179.	0.5	1
11	(Invited) Cutting-Edge Epitaxial Processes for Sub 3 Nm Technology Nodes: Application to Nanosheet Stacks and Epitaxial Wrap-Around Contacts. ECS Transactions, 2021, 104, 139-146.	0.5	3
12	Crystalline defect analysis in epitaxial Si0.7Ge0.3 layer using site-specific ECCI-STEM. Micron, 2021, 150, 103123.	2.2	3
13	60Gb/s waveguide-coupled O-band GeSi quantum-confined Stark effect electro-absorption modulator. , 2021, , .		8
14	Lowâ€Temperature Selective Growth of Heavily Boronâ€Doped Germanium Source/Drain Layers for Advanced pMOS Devices. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900628.	1.8	5
15	High Absorption Contrast Quantum Confined Stark Effect in Ultra-Thin Ge/SiGe Quantum Well Stacks Grown on Si. IEEE Journal of Quantum Electronics, 2020, 56, 1-7.	1.9	16
16	Enhancing the defect contrast in ECCI through angular filtering of BSEs. Ultramicroscopy, 2020, 210, 112922.	1.9	6
17	Source/Drain Materials for Ge nMOS Devices: Phosphorus Activation in Epitaxial Si, Ge, Ge_{1â^’x}Sn_x and Si_yGe_{1â^’xâ^’y}Sn_x. ECS Journal of Solid State Science and Technology, 2020, 9, 044010.	1.8	5
18	On the Correlation Between Static and Low-Frequency Noise Parameters of Vertical Nanowire nMOSFETs. ECS Transactions, 2020, 97, 59-64.	0.5	1

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19	A demonstration of donor passivation through direct formation of V-As<i>i</i> complexes in As-doped Ge1âˆ’<i>x</i>Sn<i>x</i>. Journal of Applied Physics, 2020, 127, .	2.5	2
20	Toward high-performance and reliable Ge channel devices for 2 nm node and beyond. , 2020, , .		9
21	Development of germanium-on-germanium engineered substrates for III-V multijunction solar cells. , 2020, , .		4
22	Contact Resistivity of Highly Doped Si:P, Si:As, and Si:P:As Epi Layers for Source/Drain Epitaxy. ECS Transactions, 2020, 98, 37-42.	0.5	9
23	On the Correlation Between Static and Low-Frequency Noise Parameters of Vertical Nanowire nMOSFETs. ECS Meeting Abstracts, 2020, MA2020-01, 1394-1394.	0.0	0
24	O-Band GeSi Quantum-Confined Stark Effect Electro-Absorption Modulator Integrated in a 220nm Silicon Photonics Platform. , 2020, , .		3
25	(Invited) Stress Simulations of Fins, Wires, and Nanosheets. ECS Transactions, 2020, 98, 253-265.	0.5	7
26	Epitaxial Ge-on-Nothing Virtual Substrates for 3D Device Stacking Technologies. ECS Transactions, 2020, 98, 195-201.	0.5	0
27	(Invited) Highly Doped Si_{1-X}Ge_x Epitaxy in View of S/D Applications. ECS Transactions, 2020, 98, 27-36.	0.5	3
28	Epitaxial Growth of Active Si on Top of SiGe Etch Stop Layer in View of 3D Device Integration. ECS Transactions, 2020, 98, 157-166.	0.5	0
29	Investigation of Low Temperature Epitaxial SiGe:P in View of Source/Drain Application for 5nm Technology Node and Below. ECS Transactions, 2020, 98, 43-50.	0.5	0
30	Epitaxial Ge-on-Nothing Virtual Substrates for 3D Device Stacking Technologies. ECS Meeting Abstracts, 2020, MA2020-02, 1764-1764.	0.0	0
31	(Invited) Highly Doped Si_{1-X}Ge_x Epitaxy in View of S/D Applications. ECS Meeting Abstracts, 2020, MA2020-02, 1731-1731.	0.0	0
32	Investigation of Low Temperature Epitaxial SiGe:P in View of Source/Drain Application for 5nm Technology Node and Below. ECS Meeting Abstracts, 2020, MA2020-02, 1735-1735.	0.0	0
33	Contact Resistivity of Highly Doped Si:P, Si:As, and Si:P:As Epi Layers for Source/Drain Epitaxy. ECS Meeting Abstracts, 2020, MA2020-02, 1733-1733.	0.0	0
34	(Invited) Stress Simulations of Fins, Wires, and Nanosheets. ECS Meeting Abstracts, 2020, MA2020-02, 1737-1737.	0.0	1
35	Epitaxial Growth of Active Si on Top of SiGe Etch Stop Layer in View of 3D Device Integration. ECS Meeting Abstracts, 2020, MA2020-02, 1640-1640.	0.0	0
36	B and Ga Co-Doping in Epitaxial SiGe: Challenges and Opportunities. ECS Meeting Abstracts, 2020, MA2020-02, 1732-1732.	0.0	0

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37	Very Low Temperature Epitaxy of Group-IV Semiconductors for Use in FinFET, Stacked Nanowires and Monolithic 3D Integration. ECS Journal of Solid State Science and Technology, 2019, 8, P392-P399.	1.8	15
38	Epitaxial Growth of Ga-doped SiGe for Reduction of Contact Resistance in finFET Source/Drain Materials. ECS Transactions, 2019, 93, 7-10.	0.5	5
39	TEM investigations of gate-all-around nanowire devices. Semiconductor Science and Technology, 2019, 34, 124003.	2.0	4
40	Epitaxial Growth of (Si)GeSn Source/Drain Layers for Advanced Ge Gate All Around Devices. , 2019, , .		0
41	Heavily phosphorus doped germanium: Strong interaction of phosphorus with vacancies and impact of tin alloying on doping activation. Journal of Applied Physics, 2019, 125, .	2.5	6
42	Insights into the C Distribution in Si:C/Si:C:P and the Annealing Behavior of Si:C Layers. ECS Journal of Solid State Science and Technology, 2019, 8, P209-P216.	1.8	0
43	Low temperature epitaxial growth of Ge:B and Ge0.99Sn0.01:B source/drain for Ge pMOS devices: in-situ and conformal B-doping, selectivity towards oxide and nitride with no need for any post-epi activation treatment. Japanese Journal of Applied Physics, 2019, 58, SBBA04.	1.5	11
44	Evolution of phosphorus-vacancy clusters in epitaxial germanium. Journal of Applied Physics, 2019, 125, .	2.5	13
45	A record Gm_{SAT}/SS_{SAT} and PBTI reliability in Si-passivated Ge nFinFETs by improved gate stack surface preparation. , 2019, , .		11
46	Vertical Nanowire and Nanosheet FETs: Device Features, Novel Schemes for Improved Process Control and Enhanced Mobility, Potential for Faster & More Energy Efficient Circuits. , 2019, , .		18
47	Device-Based Threading Dislocation Assessment in Germanium Hetero-Epitaxy. , 2019, , .		1
48	Record Gm_{SAT}/SS_{SAT} and PBTI Reliability in Si-Passivated Ge nFinFETs by Improved Gate-Stack Surface Preparation. IEEE Transactions on Electron Devices, 2019, 66, 5387-5392.	3.0	4
49	Characterization of Highly Doped Si:P, Si:As and Si:P:As Epi Layers for Source/Drain Epitaxy. ECS Transactions, 2019, 93, 11-15.	0.5	3
50	Source/Drain Materials for Ge nMOS Devices. ECS Transactions, 2019, 93, 29-33.	0.5	1
51	Impact of Ge-Oxide-Scavenging on Low-T Steam Oxidation and Passivation of Bi-Axially Strained Si0.75Ge0.25. ECS Transactions, 2019, 93, 71-72.	0.5	1
52	Application of Cl₂ for low temperature etch and epitaxy. Semiconductor Science and Technology, 2019, 34, 074003.	2.0	2
53	Scalability comparison between raised- and embedded-SiGe source/drain structures for Si 0.55 Ge 0.45 implant free quantum well pFET. Microelectronics Reliability, 2018, 83, 157-161.	1.7	1
54	Editors' Choiceâ€”Epitaxial CVD Growth of Ultra-Thin Si Passivation Layers on Strained Ge Fin Structures. ECS Journal of Solid State Science and Technology, 2018, 7, P66-P72.	1.8	17

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55	Enhanced B doping in CVD-grown GeSn:B using B Î´-doping layers. Journal of Crystal Growth, 2018, 483, 285-290.	1.5	6
56	On the Evolution of Strain and Electrical Properties in As-Grown and Annealed Si:P Epitaxial Films for Source-Drain Stressor Applications. ECS Journal of Solid State Science and Technology, 2018, 7, P228-P237.	1.8	4
57	Non-destructive characterization of extended crystalline defects in confined semiconductor device structures. Nanoscale, 2018, 10, 7058-7066.	5.6	22
58	Advantage of NW structure in preservation of SRB-induced strain and investigation of off-state leakage in strained stacked Ge NW pFET. , 2018, , .		14
59	An In-depth Study of High-Performing Strained Germanium Nanowires pFETs. , 2018, , .		10
60	Defect evaluation in strain-relaxed Ge0.947Sn0.053 grown on (001) Si. Applied Physics Letters, 2018, 113, 192103.	3.3	0
61	First demonstration of vertically-stacked Gate-All-Around highly-strained Germanium nanowire p-FETs. , 2018, , .		6
62	Ascertaining the Nature and Distribution of Extended Crystalline Defects in Emerging Semiconductor Materials Using Electron Channeling Contrast Imaging. ECS Transactions, 2018, 86, 387-396.	0.5	3
63	Impact of band to band tunneling in In0.53Ga0.47As tunnel diodes on the deep level transient spectra. Applied Physics Letters, 2018, 113, 232101.	3.3	1
64	(Invited) Very Low Temperature Epitaxy of Group-IV Semiconductors for Use in FinFET, Stacked Nanowires and Monolithic 3D Integration. ECS Transactions, 2018, 86, 163-175.	0.5	7
65	(Invited) Determining Si Composition in SiGe Alloys with < 1% Si Concentrations Using Raman Spectroscopy. ECS Transactions, 2018, 86, 397-407.	0.5	1
66	Epitaxial GeSn: impact of process conditions on material quality. Semiconductor Science and Technology, 2018, 33, 114010.	2.0	20
67	First Demonstration of Vertically Stacked Gate-All-Around Highly Strained Germanium Nanowire pFETs. IEEE Transactions on Electron Devices, 2018, 65, 5145-5150.	3.0	46
68	Carrier scattering induced linewidth broadening in <i>in situ</i> P-doped Ge layers on Si. Applied Physics Letters, 2018, 113, .	3.3	8
69	Electrical properties of extended defects in strain relaxed GeSn. Applied Physics Letters, 2018, 113, 022102.	3.3	18
70	Atomically Controlled Processing for Dopant Segregation in CVD Si and Ge Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2018, 7, P305-P310.	1.8	5
71	(Invited) Very Low Temperature Epitaxy of Group-IV Semiconductors for Use in Finfet, Stacked Nanowires and Monolithic 3D Integration. ECS Meeting Abstracts, 2018, , .	0.0	0
72	Ascertaining the Nature and Distribution of Extended Crystalline Defects in Emerging Semiconductor Materials Using Electron Channeling Contrast Imaging. ECS Meeting Abstracts, 2018, , .	0.0	0

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73	(Invited) Determining Si Composition in SiGe Alloys with < 1% Si concentrations using Raman Spectroscopy. ECS Meeting Abstracts, 2018, , .	0.0	0
74	High-contrast quantum-confined Stark effect in Ge/SiGe quantum well stacks on Si with ultra-thin buffer layers. , 2018, , .		2
75	Processing Technologies for Advanced Ge Devices. ECS Journal of Solid State Science and Technology, 2017, 6, P14-P20.	1.8	30
76	Observation and understanding of anisotropic strain relaxation in selectively grown SiGe fin structures. Nanotechnology, 2017, 28, 145703.	2.6	10
77	Fundamentals of Ge 1âˆ’x Sn x and Si y Ge 1âˆ’x-y Sn x RPCVD epitaxy. Materials Science in Semiconductor Processing, 2017, 70, 38-43.	4.0	36
78	Study of SiGe Surface Cleaning. ECS Transactions, 2017, 80, 141-146.	0.5	0
79	Investigation of Cl₂etch in view of extremely low temperature selective epitaxial processes. Semiconductor Science and Technology, 2017, 32, 114006.	2.0	9
80	(Invited) Challenges on Surface Conditioning in 3D Device Architectures: Triple-Gate FinFETs, Gate-All-Around Lateral and Vertical Nanowire FETs. ECS Transactions, 2017, 80, 3-20.	0.5	6
81	(Invited) Atomically Controlled Processing for Dopant Segregation in CVD Silicon and Germanium Epitaxial Growth. ECS Transactions, 2017, 79, 33-42.	0.5	0
82	Fabrication, Characterization, and Analysis of Ge/GeSn Heterojunction p-Type Tunnel Transistors. IEEE Transactions on Electron Devices, 2017, 64, 4354-4362.	3.0	27
83	Photoluminescence of phosphorus atomic layer doped Ge grown on Si. Semiconductor Science and Technology, 2017, 32, 104005.	2.0	1
84	Local Arrangement of Substitutional C Atoms and the Thermal Stability of Epitaxial Si:C(P) Grown by CVD. ECS Journal of Solid State Science and Technology, 2017, 6, P755-P759.	1.8	3
85	Carbon-Related Defects in Si:C/Silicon Heterostructures Assessed by Deep-Level Transient Spectroscopy. ECS Journal of Solid State Science and Technology, 2017, 6, P284-P289.	1.8	5
86	Use of high order precursors for manufacturing gate all around devices. Materials Science in Semiconductor Processing, 2017, 70, 24-29.	4.0	24
87	Reliable 50Gb/s silicon photonics platform for next-generation data center optical interconnects. , 2017, , .		19
88	(Invited) Epitaxial CVD Growth of Ultra-Thin Si Passivation Layers on Strained Ge Fin Structures. ECS Transactions, 2017, 80, 241-252.	0.5	0
89	Strained Germanium Gate-All-Around pMOS Device Demonstration Using Selective Wire Release Etch Prior to Replacement Metal Gate Deposition. IEEE Transactions on Electron Devices, 2017, 64, 4587-4593.	3.0	45
90	Strained germanium gate-all-around PMOS device demonstration using selective wire release etch prior to replacement metal gate deposition. , 2017, , .		8

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91	Analysis of homogeneous broadening in n-type doped Ge layers on Si for laser application. , 2017, , .		1
92	Reduction of optical bleaching in phosphorus doped Ge layer on Si. , 2017, , .		0
93	Performance and electrostatic improvement by high-pressure anneal on Si-passivated strained Ge pFinFET and gate all around devices with superior NBTI reliability. , 2017, , .		13
94	Strain and Compositional Analysis of (Si)Ge Fin Structures Using High Resolution Xâ€Ray Diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, .	0.8	7
95	On the manifestation of phosphorus-vacancy complexes in epitaxial Si:P films. Applied Physics Letters, 2016, 108, .	3.3	15
96	Design Requirements for Group-IV Laser Based on Fully Strained Ge_{1âˆ’x}Sn_xEmbedded in Partially Relaxed Si_{1âˆ’yâˆ’z}Ge_ySn_zBuffer Layers. ECS Journal of Solid State Science and Technology, 2016, 5, Q140-Q143.	1.8	7
97	(Invited) Processing Technologies for Advanced Ge Devices. ECS Transactions, 2016, 75, 491-503.	0.5	4
98	Laser annealed in-situ P-doped Ge for on-chip laser source applications (Conference Presentation). , 2016, , .		0
99	Performance benchmarking of p-type In<inf>0.65</inf>Ga<inf>0.35</inf>As/GaAs<inf>0.4</inf>Sb<inf>0.6</inf> and Ge/Ge<inf>0.93</inf>Sn<inf>0.07</inf> hetero-junction tunnel FETs. , 2016, , .		10
100	Si-passivated Ge nMOS gate stack with low Dit and dipole-induced superior PBTI reliability using 3D-compatible ALD caps and high-pressure anneal. , 2016, , .		13
101	Study of electrically active defects in epitaxial layers on silicon. , 2016, , .		0
102	Density and Capture Cross-Section of Interface Traps in GeSnO₂ and GeO₂ Grown on Heteroepitaxial GeSn. ACS Applied Materials & Interfaces, 2016, 8, 13181-13186.	8.0	23
103	ICSI-9, MontrÃ©al 2015: Silicon for now and beyond. Thin Solid Films, 2016, 602, 1-2.	1.8	0
104	A 2nd Generation of 14/16nm-node compatible strained-Ge pFINFET with improved performance with respect to advanced Si-channel FinFETs. , 2016, , .		15
105	(Invited) Atomically Controlled Processing for Si and Ge CVD Epitaxial Growth. ECS Transactions, 2016, 72, 71-82.	0.5	2
106	(Invited) Selective Epitaxial Growth of High-P Si:P for Source/Drain Formation in Advanced Si nFETs. ECS Transactions, 2016, 75, 347-359.	0.5	37
107	Substitutional Carbon Loss in Si:C Stressor Layers Probed by Deep-Level Transient Spectroscopy. ECS Transactions, 2016, 75, 3-11.	0.5	2
108	Atomically controlled processing for Ge CVD epitaxial growth. , 2016, , .		0

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109	Influence of precursor gas on SiGe epitaxial material quality in terms of structural and electrical defects. Japanese Journal of Applied Physics, 2016, 55, 04EJ11.	1.5	0
110	Reviewâ€"Device Assessment of Electrically Active Defects in High-Mobility Materials. ECS Journal of Solid State Science and Technology, 2016, 5, P3149-P3165.	1.8	18
111	Silicon-based Photonic Integrated Circuits for the Mid-infrared. Procedia Engineering, 2016, 140, 144-151.	1.2	8
112	Enhanced active P doping by using high order Ge precursors leading to intense photoluminescence. Thin Solid Films, 2016, 602, 56-59.	1.8	19
113	Properties and growth peculiarities of Si0.30Ge0.70 stressor integrated in 14nm fin-based p-type metal-oxide-semiconductor field-effect transistors. Thin Solid Films, 2016, 602, 72-77.	1.8	15
114	Interplay between relaxation and Sn segregation during thermal annealing of GeSn strained layers. Journal of Applied Physics, 2016, 120, .	2.5	21
115	50Gb/s C-band GeSi Waveguide Electro-Absorption Modulator. , 2016, , .		14
116	(Invited) On the Electrical Activity of Extended Defects in High-Mobility Channel Materials. ECS Transactions, 2015, 69, 119-130.	0.5	5
117	On the interplay between relaxation, defect formation, and atomic Sn distribution in Ge(1â^'x)Sn(x) unraveled with atom probe tomography. Journal of Applied Physics, 2015, 118, .	2.5	13
118	Ge nFET with high electron mobility and superior PBTI reliability enabled by monolayer-Si surface passivation and La-induced interface dipole formation. , 2015, , .		24
119	(Invited) Selective Etch of Si and SiGe for Gate All-Around Device Architecture. ECS Transactions, 2015, 69, 147-152.	0.5	20
120	Strained germanium quantum well p-FinFETs fabricated on 45nm Fin pitch using replacement channel, replacement metal gate and germanide-free local interconnect. , 2015, , .		28
121	Chemical vapor deposition of Si:C and Si:C:P filmsâ€"Evaluation of material quality as a function of C content, carrier gas and doping. Journal of Crystal Growth, 2015, 426, 75-81.	1.5	10
122	(Invited) Heterogeneous Nano- to Wide-Scale Co-Integration of Beyond-Si and Si CMOS Devices to Enhance Future Electronics. ECS Transactions, 2015, 66, 3-14.	0.5	6
123	Electrical characterization of p-GeSn/n-Ge diodes with interface traps under dc and ac regimes. Solid-State Electronics, 2015, 110, 65-70.	1.4	10
124	Amorphous inclusions during Ge and GeSn epitaxial growth via chemical vapor deposition. Thin Solid Films, 2015, 590, 163-169.	1.8	11
125	Extended X-ray absorption fine structure investigation of Sn local environment in strained and relaxed epitaxial Ge1â^'xSnx films. Journal of Applied Physics, 2015, 117, .	2.5	24
126	TCAD Strain Calibration Versus Nanobeam Diffraction of Source/Drain Stressors for Ge MOSFETs. IEEE Transactions on Electron Devices, 2015, 62, 1079-1084.	3.0	8

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127	Ultimate nano-electronics: New materials and device concepts for scaling nano-electronics beyond the Si roadmap. Microelectronic Engineering, 2015, 132, 218-225.	2.4	30
128	15nm-W<inf>FIN</inf> high-performance low-defectivity strained-germanium pFinFETs with low temperature STI-last process. , 2014, , .		20
129	Use of X-ray techniques in the development and production of novel transistor structures. , 2014, , .		0
130	High-Performance Si_{0.45}Ge_{0.55}Implant-Free Quantum Well pFET With Enhanced Mobility by Low-Temperature Process and Transverse Strain Relaxation. IEEE Transactions on Electron Devices, 2014, 61, 3985-3990.	3.0	2
131	Compressively strained SiGe band-to-band tunneling model calibration based on p-i-n diodes and prospect of strained SiGe tunneling field-effect transistors. Journal of Applied Physics, 2014, 116, 214506.	2.5	22
132	Ge-on-Si and Ge-on-SOI thermo-optic phase shifters for the mid-infrared. Optics Express, 2014, 22, 28479.	3.4	100
133	Ge-Source Vertical Tunnel FETs Using a Novel Replacement-Source Integration Scheme. IEEE Transactions on Electron Devices, 2014, 61, 4032-4039.	3.0	36
134	Band alignment at interfaces of amorphous Al2O3 with Ge1â^’xSnx- and strained Ge-based channels. Applied Physics Letters, 2014, 104, 202107.	3.3	4
135	(Invited) High Ge Content SiGe Thin Films: Growth, Properties and Integration. ECS Transactions, 2014, 64, 831-839.	0.5	10
136	Long-wavelength silicon photonic integrated circuits. , 2014, , .		0
137	(Invited) Positron Annihilation Spectroscopy on Open-Volume Defects in Group IV Semiconductors. ECS Transactions, 2014, 64, 241-253.	0.5	1
138	(Invited) Ge_{1-x}Sn_x Optical Devices: Growth and Applications. ECS Transactions, 2014, 64, 677-687.	0.5	3
139	First demonstration of 15nm-W<inf>FIN</inf> inversion-mode relaxed-Germanium n-FinFETs with Si-cap free RMG and NiSiGe Source/Drain. , 2014, , .		15
140	Evaluation of the Si0.8Ge0.2-on-Si Epitaxial Quality by Inline Surface Light Scattering: A Case Study on the Impact of Interfacial Oxygen. ECS Transactions, 2014, 64, 989-995.	0.5	3
141	Characterization of Epitaxial Si:C:P and Si:P Layers for Source/Drain Formation in Advanced Bulk FinFETs. ECS Transactions, 2014, 64, 977-987.	0.5	45
142	Catalyst Assisted Low Temperature Pre Epitaxial Cleaning for Si and SiGe Surfaces. Solid State Phenomena, 2014, 219, 16-19.	0.3	1
143	Use of a Purged FOUP to Improve H-Terminated Silicon Surface Stability Prior to Epitaxial Growth. ECS Transactions, 2014, 64, 669-673.	0.5	2
144	Chemical vapor deposition processes for the fabrication of epitaxial Si-O superlattices. Thin Solid Films, 2014, 557, 36-41.	1.8	9

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145	Fabrication and Analysis of a ${m Si}/{m Si}_{0.55}{m Ge}_{0.45}$ Heterojunction Line Tunnel FET. IEEE Transactions on Electron Devices, 2014, 61, 707-715.	3.0	123
146	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	2.9	106
147	Optimized design of Si-cap layer in strained-SiGe channel p-MOSFETs based on computational and experimental approaches. Solid-State Electronics, 2014, 91, 1-8.	1.4	5
148	Electrical characterization of pGeSn/nGe diodes. , 2014, , .		0
149	Comparison between experimental and simulated strain profiles in Ge channels with embedded source/drain stressors. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1578-1582.	0.8	5
150	Material Studies on Si:C Epitaxial Films Grown by CVD. ECS Transactions, 2014, 64, 997-1005.	0.5	1
151	Strained Ge FinFET structures fabricated by selective epitaxial growth. , 2014, , .		6
152	(Invited) Application of Selective Epitaxial Growth in the Sub 20 nm FinFET Device Fabrication. ECS Transactions, 2014, 60, 497-502.	0.5	6
153	Impact of stressors in future SiGe-based FinFETs: Mobility boost and scalability. , 2014, , .		0
154	Defect assessment and leakage control in Ge junctions. Microelectronic Engineering, 2014, 125, 33-37.	2.4	18
155	Identification of Deep Levels Associated with Extended and Point Defects in GeSn Epitaxial Layers Using DLTs. ECS Transactions, 2013, 53, 251-258.	0.5	7
156	Mid-IR heterogeneous silicon photonics. Proceedings of SPIE, 2013, , .	0.8	2
157	Germanium-on-silicon planar concave grating wavelength (de)multiplexers in the mid-infrared. Applied Physics Letters, 2013, 103, .	3.3	66
158	Integration aspects of strained Ge pFETs. , 2013, , .		1
159	Stress Techniques and Mobility Enhancement in FinFET Architectures. ECS Transactions, 2013, 50, 47-58.	0.5	7
160	A new complementary hetero-junction vertical Tunnel-FET integration scheme. , 2013, , .		50
161	Analysis of trap-assisted tunneling in vertical Si homo-junction and SiGe hetero-junction Tunnel-FETs. Solid-State Electronics, 2013, 83, 50-55.	1.4	117
162	Germanium-on-Silicon Mid-Infrared Arrayed Waveguide Grating Multiplexers. IEEE Photonics Technology Letters, 2013, 25, 1805-1808.	2.5	127

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163	(Invited) Stress Simulations of Si- and Ge-Channel FinFETs for the 14 nm-Node and Beyond. ECS Transactions, 2013, 53, 225-236.	0.5	3
164	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	3.0	65
165	Orientation Dependence of Si_{1-x}C_x:P Growth and the Impact on FinFET Structures. ECS Transactions, 2013, 50, 491-497.	0.5	4
166	Crystalline Properties and Strain Relaxation Mechanism of CVD Grown GeSn. ECS Transactions, 2013, 50, 875-883.	0.5	8
167	High Ge Content SiGe Selective Processes for Manufacturing Source/Drain in the Next Generations of pMOS Transistors. ECS Transactions, 2013, 50, 807-814.	0.5	0
168	SiGe Band-to-Band Tunneling Calibration based on p-i-n Diodes: Fabrication, Measurement and Simulation. ECS Transactions, 2013, 50, 965-970.	0.5	4
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